

N-Ch MOSFET

General Description

The WST6002 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST6002 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- High-speed switching
- Green Device Available
- ESD Protected:2KV

Product Summery

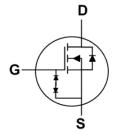
BVDSS	RDSON	ID
30V	5Ω	100mA

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC
- Networking DC-DC Power System
- Load Switch

SOT-523 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	100	mA
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	60	mA
I _{DM}	Pulsed Drain Current ²	0.5	Α
P _D @T _A =25°C	Total Power Dissipation ³	0.15	W
T _{STG}	Storage Temperature Range -55 to 1		${\mathbb C}$
T _J	Operating Junction Temperature Range	-55 to 150	${\mathbb C}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-Ambient ¹		625	°C/W



Electrical Characteristics (T_J=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.05		V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =0.01A			5	Ω
		V _{GS} =4.5V , I _D =0.01A			13	
V _{GS(th)}	Gate Threshold Voltage	., .,	1		2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$-V_{GS}=V_{DS}$, $I_D=250uA$		-3.7		mV/℃
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25℃			1	
		V_{DS} =24V , V_{GS} =0V , T_J =55 $^{\circ}$ C			5	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±10	uA
gfs	Forward Transconductance	V _{DS} =5V , I _D =0.1A		450		mS
$T_{d(on)}$	Turn-On Delay Time			2	3.5	
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		1.0	2.2	200
$T_{d(off)}$	Turn-Off Delay Time	$R_G=3.3\Omega, I_D=0.1A$		5	9	ns
T_f	Fall Time			1.5	2.5	
C _{iss}	Input Capacitance			9		
C _{oss}	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		5		pF
C _{rss}	Reverse Transfer Capacitance			2		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V =V =0V Force Current			100	mA
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			0.5	Α
V_{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_S =0.2A , T_J =25 $^{\circ}$ C			1	V

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%
- 3.The power dissipation is limited by 150 ℃ junction temperature.
- 4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

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Typical Characteristics

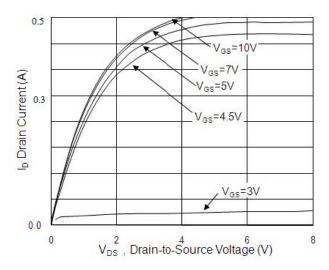


Fig.1 Typical Output Characteristics

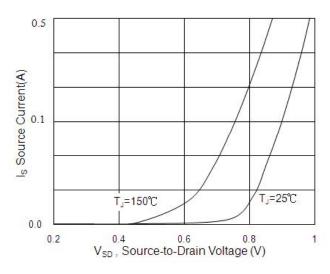


Fig.3 Forward Characteristics of Reverse

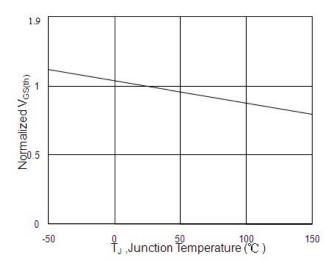


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

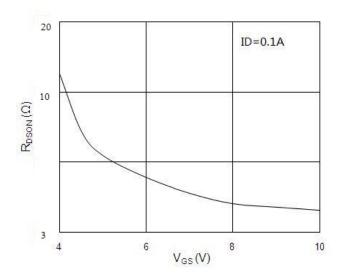


Fig.2 On-Resistance vs. Gate-Source Voltage

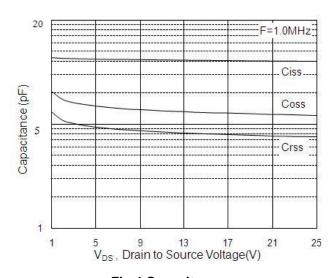


Fig.4 Capacitance

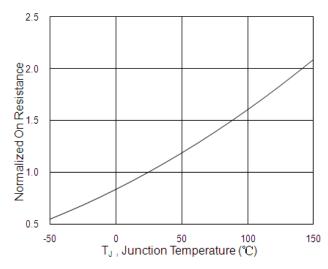
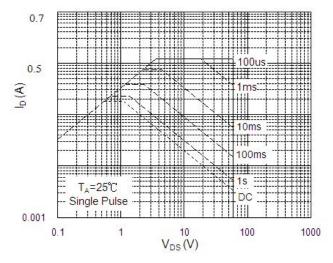


Fig.6 Normalized R_{DSON} vs. T_J



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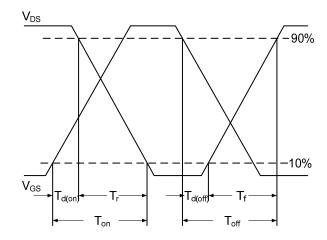


Fig.8 Safe Operating Area

Fig.10 Switching Time Waveform

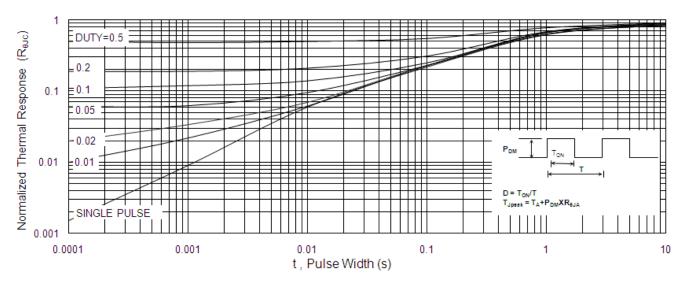


Fig.9 Normalized Maximum Transient Thermal Impedance



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